ABSTRACT

SPUTTERING TARGET OF MAGNETIC MATERIAL

[Abstract] A magnetic sputtering target which contains B and is obtained by a melting and casting method, wherein the B content is 10 at% or more and 50 at% or less, and the remainder is one or more elements selected from Co, Fe, and Ni. Based on the method of the present invention, the sputtering target, in which gaseous impurities are few, there are no cracks and fractures, and segregation of its main constituent elements is minimal, is obtained. Consequently, when sputtered with a magnetron sputtering device comprising a DC power supply, this sputtering target yields a significant effect of being able to inhibit the generation of particles during sputtering, and improve the production yield upon forming thin films.